List of impacted publications used as part of dissertation:

1. F. Hájek, V. Jarý, T. Hubáček, F. Dominec, A. Hospodková, K. Kuldová, J. Oswald, J. Pangrác, T. Vaněk, M. Buryi, G. Ledoux, C. Dujardin
   Donor-Acceptor pairs recombination as the origin of the emission shift in InGaN/GaN scintillator heterostructures doped with Zn
   Radiation Measurements ?? (2023), ?? (*in process*)
2. A. Hospodková, J. Čížek, F. Hájek, T. Hubáček, J. Pangrác, F. Dominec, K. Kuldová, J. Batysta, M.O. Liedke, E. Hirschmann, M. Butterling, A. Wagner
   Relation between Ga Vacancies, Photoluminescence, and Growth Conditions of MOVPE-Prepared GaN Layers
   Materials 15 (2022) 6916(1) - 6916(13).
3. T. Vaněk, V. Jarý, T. Hubáček, F. Hájek, K. Kuldová, Z. Gedeonová, V. Babin, Z. Remeš, M. Buryi
   Acceleration of the yellow band luminescence in GaN layers via Si and Ge doping
   J. Alloy. Compd. 914 (2022) 165255
4. F. Hájek, A. Hospodková, T. Hubáček, J. Oswald, J. Pangrác, F. Dominec, R. Horešovský, K. Kuldová
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5. T. Vaněk, F. Hájek, F. Dominec, T. Hubáček, K. Kuldová, J. Pangrác, T. Košutová, P. Kejzlar, P. Bábor, A. Lachowski, A. Hospodková
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List of other impacted publications with FNSPE affiliation:

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   Peculiarities of erbium incorporation into ZnO microrods at high doping level leading to upconversion and the morphology change. Influence on excitonic as well as shallow donor states
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8. A. Hospodková, F. Hájek, T. Hubáček, Z. Gedeonová, P. Hubík, J.J. Mareš, J. Pangrác, F. Dominec, K. Kuldová, E. Hulicius
   Electron mobility in GaN layers and HEMT structure optimized by MOVPE technological parameters
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9. T. Hubáček, K. Kuldová, Z. Gedeonová, F. Hájek, T. Košutová, S. Banerjee, P. Hubík, J. Pangrác, T. Vaněk, A. Hospodková
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14. F. Hájek, A. Hospodková, P. Hubík, Z. Gedeonová, T. Hubáček, J. Pangrác, K. Kuldová
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2. T. Hubáček, A. Hospodková, K. Kuldová, J. Oswald, J. Pangrác, V. Jarý, F. Dominec, M. Slavická Zíková, F. Hájek, E. Hulicius, A. Vetushka, G. Ledoux, Ch. Dujardin, M. Nikl
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